

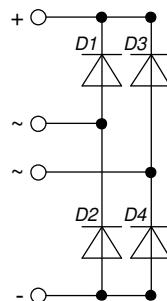
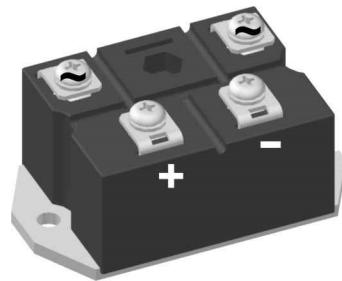
Standard Rectifier Module

1~ Rectifier
$V_{RRM} = 1800 \text{ V}$
$I_{DAV} = 60 \text{ A}$
$I_{FSM} = 550 \text{ A}$

1~ Rectifier Bridge

Part number

VBO52-18NO7



 E72873

Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For one phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-D

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

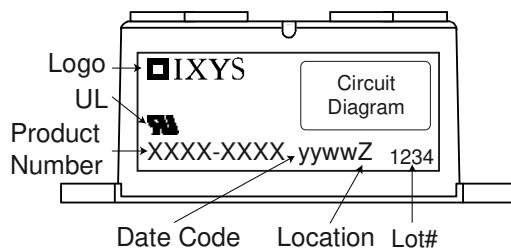
Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

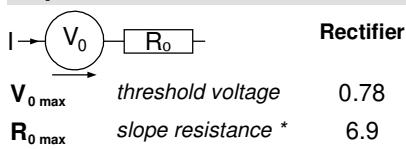
Rectifier

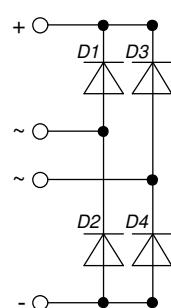
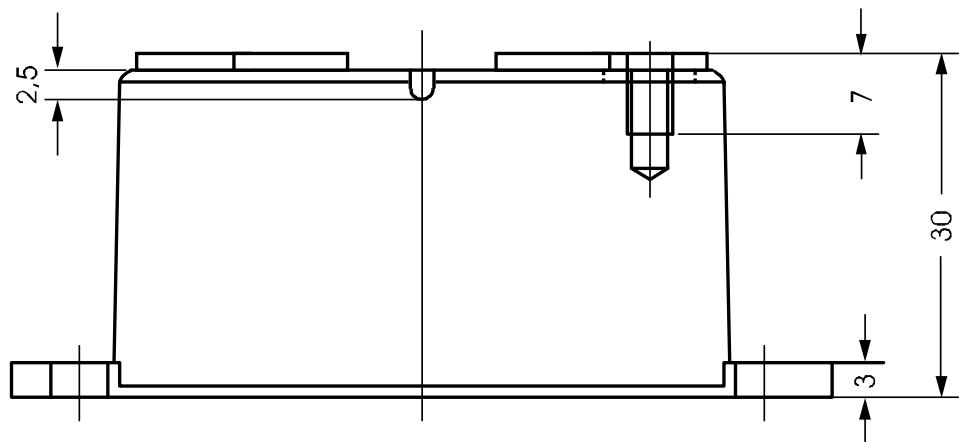
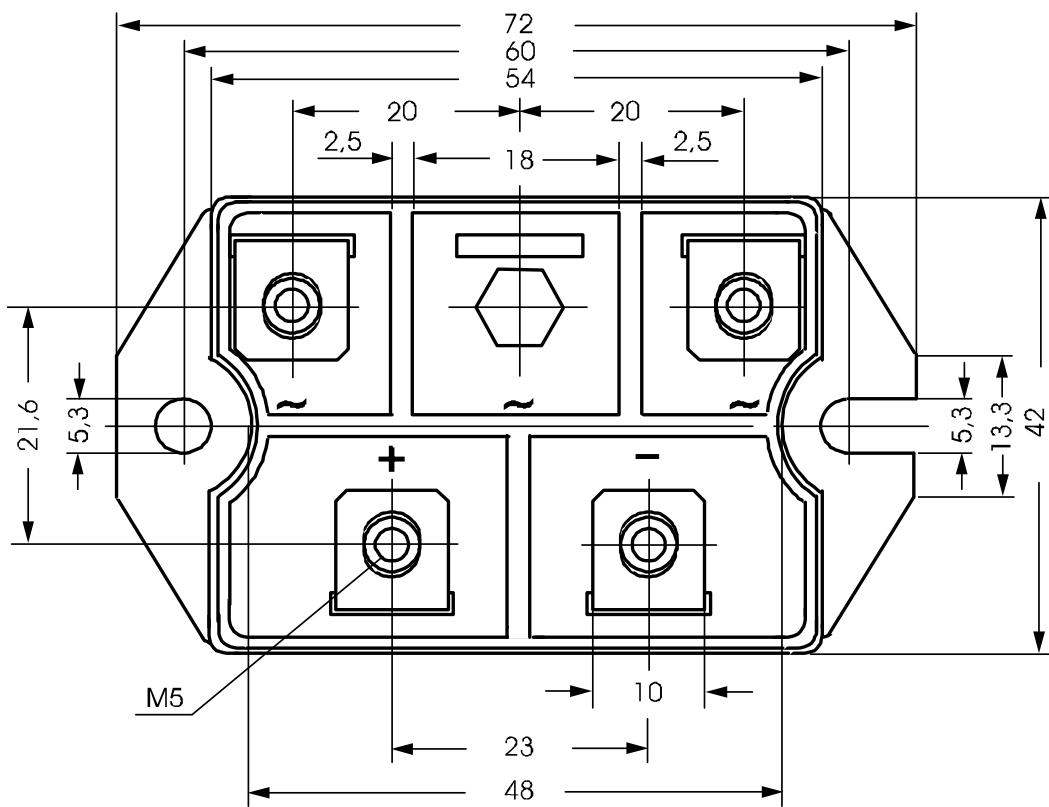
Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1900	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1800	V
I_R	reverse current	$V_R = 1800 \text{ V}$ $V_R = 1800 \text{ V}$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		40 1.5	μA mA
V_F	forward voltage drop	$I_F = 20 \text{ A}$ $I_F = 40 \text{ A}$ $I_F = 20 \text{ A}$ $I_F = 40 \text{ A}$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		1.07 1.19 0.96 1.13	V V
I_{DAV}	bridge output current	$T_C = 115^\circ C$ rectangular $d = 0.5$	$T_{VJ} = 150^\circ C$		60	A
V_{F0} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ C$		0.78 8.1	V $m\Omega$
R_{thJC}	thermal resistance junction to case				1.1	K/W
R_{thCH}	thermal resistance case to heatsink				0.4	K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		110	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 \text{ V}$ $T_{VJ} = 150^\circ C$ $V_R = 0 \text{ V}$		550 595 470 505	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 \text{ V}$ $T_{VJ} = 150^\circ C$ $V_R = 0 \text{ V}$		1.52 1.48 1.11 1.06	kA ² s kA ² s kA ² s kA ² s
C_J	junction capacitance	$V_R = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$		19	pF

Package PWS-D			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			150	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				153		g
M_D	mounting torque		4.25		5.75	Nm
M_T	terminal torque		4.25		5.75	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air		9.5			mm
$d_{Spb/Apb}$	terminal to terminal terminal to backside		26.0			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3000 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	2500		V V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VBO52-18NO7	VBO52-18NO7	Box	10	491470

Equivalent Circuits for Simulation
* on die level
 $T_{VJ} = 150^\circ\text{C}$


Outlines PWS-D


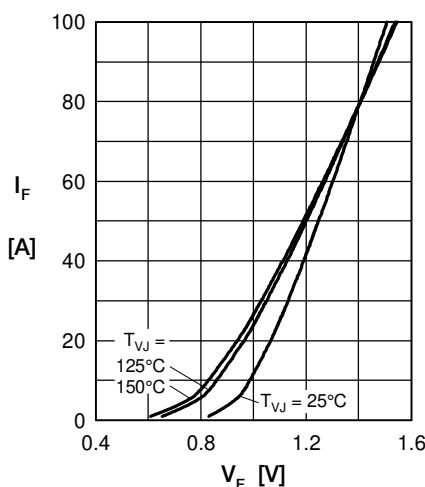
Rectifier


Fig. 1 Forward current vs.
voltage drop per diode

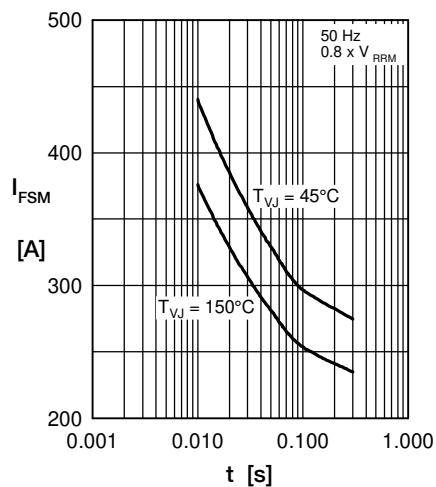


Fig. 2 Surge overload current
vs. time per diode

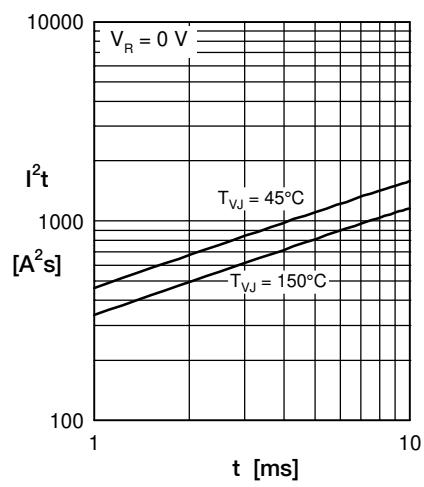


Fig. 3 I^2t vs. time per diode

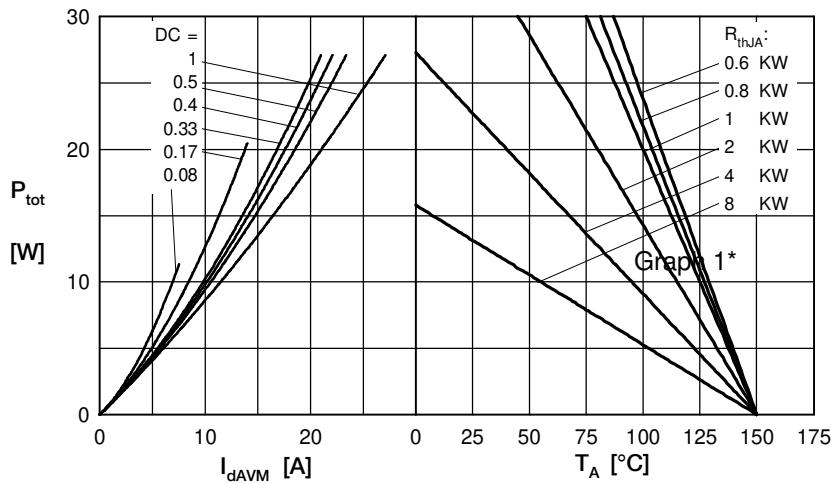


Fig. 4 Power dissipation vs. forward current
and ambient temperature per diode

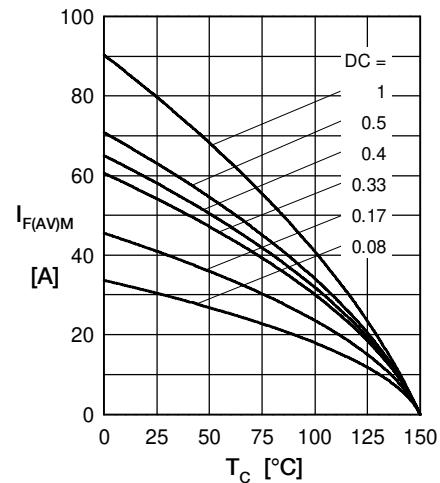


Fig. 5 Max. forward current vs.
case temperature per diode

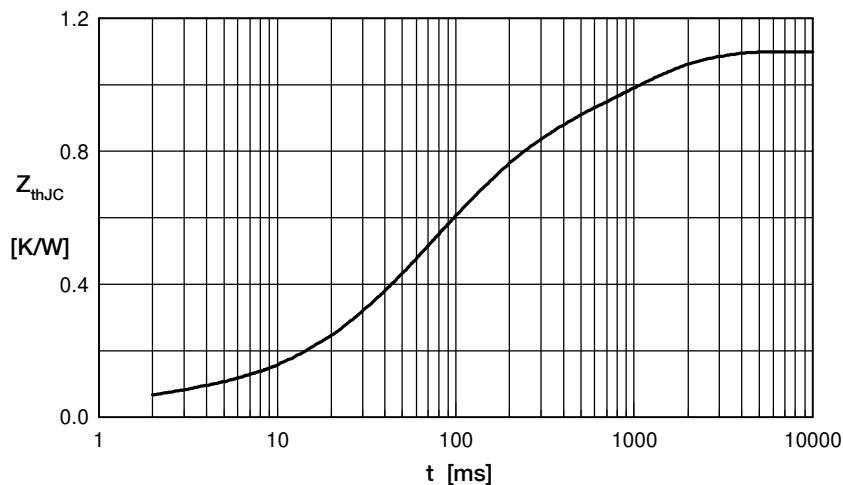


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.05	0.001
2	0.14	0.030
3	0.25	0.060
4	0.35	0.130
5	0.31	0.920

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bridge Rectifiers](#) category:

Click to view products by [IXYS manufacturer:](#)

Other Similar products are found below :

[MB2510](#) [MB252](#) [MB356G](#) [MB358G](#) [GBJ1504-BP](#) [GBU15J-BP](#) [GBU15K-BP](#) [GBU4A-BP](#) [GBU6B-E3/45](#) [GSIB680-E3/45](#) [DB101-BP](#)
[DF01](#) [DF10SA-E345](#) [KBPC50-10S](#) [RS405GL-BP](#) [G5SBA60-E3/51](#) [GBU10J-BP](#) [GBU6M](#) [GBU8D-BP](#) [GBU8J-BP](#) [GSIB1520-E3/45](#)
[2KBB10](#) [36MB140A](#) [TB102M](#) [MB1510](#) [MB258](#) [MB6M-G](#) [MB86](#) [TL401G](#) [MDA920A2](#) [TU602](#) [TU810](#) [MP501W-BP](#) [MP502-BP](#)
[BR101-BP](#) [BR84DTP204](#) [BU2008-E3/51](#) [36MB100A](#) [KBPC10/15/2501WP](#) [KBPC25-02](#) [VS-2KBB60](#) [DF06SA-E345](#) [DF1510S](#) [VS-40MT160PAPBF](#) [W02M](#) [GBL02-E3/45](#) [GBU4G-BP](#) [GBJ2506-BP](#) [GBU6B-E3/51](#) [GSIB15A80-E3/45](#)